

## P-Channel 1.8-V (G-S) MOSFET

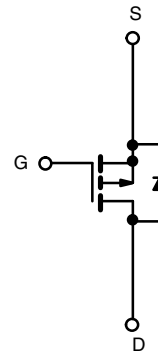
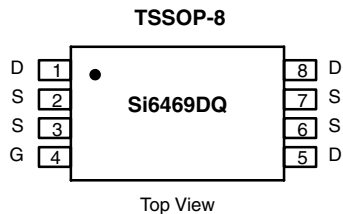
PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 8	0.028 at $V_{GS} = - 4.5$ V	$\pm 6.0$
	0.031 at $V_{GS} = - 3.3$ V	$\pm 5.8$
	0.040 at $V_{GS} = - 2.5$ V	$\pm 5.0$
	0.065 at $V_{GS} = - 1.8$ V	$\pm 3.6$

### FEATURES

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFETs: 1.8 V Rated



**RoHS**  
COMPLIANT



**Ordering Information:** Si6469DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	$V_{DS}$	- 8	V		
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a, b</sup>	$I_D$	$T_A = 25$ °C	$\pm 6.0$	A	
		$T_A = 70$ °C	$\pm 5.0$		
Pulsed Drain Current	$I_{DM}$	$\pm 30$			
Continuous Source Current (Diode Conduction) <sup>a, b</sup>	$I_S$	- 1.25			
Maximum Power Dissipation <sup>a, b</sup>	$P_D$	$T_A = 25$ °C	1.5	W	
		$T_A = 70$ °C	1.0		
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	83	°C/W	
		Steady State	95		

Notes:

a. Surface Mounted on FR4 board.

b.  $t \leq 10$  s.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>.

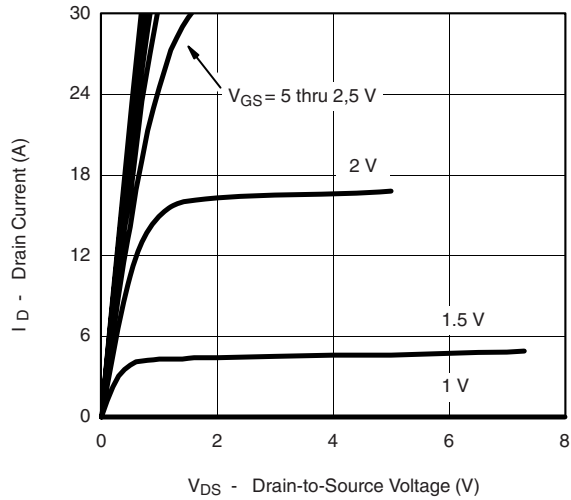
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>b</sup>	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.45			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -6.4\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -6.4\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			- 25	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq -8\text{ V}, V_{GS} = -4.5\text{ V}$	- 30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -6.0\text{ A}$		0.021	0.028	$\Omega$
		$V_{GS} = -3.3\text{ V}, I_D = -5.8\text{ A}$		0.024	0.031	
		$V_{GS} = -2.5\text{ V}, I_D = -5.0\text{ A}$		0.030	0.040	
		$V_{GS} = -1.8\text{ V}, I_D = -3.6\text{ A}$		0.048	0.065	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -8\text{ V}, I_D = -6.0\text{ A}$		18		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.25\text{ A}, V_{GS} = 0\text{ V}$		- 0.68	- 1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -6.0\text{ A}$		20	40	nC
Gate-Source Charge	$Q_{gs}$		4.5			
Gate-Drain Charge	$Q_{gd}$		3.6			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		20	50	ns
Rise Time	$t_r$		30	60		
Turn-Off Delay Time	$t_{d(off)}$		85	150		
Fall Time	$t_f$		50	90		
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -1.25\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		50	100	

## Notes:

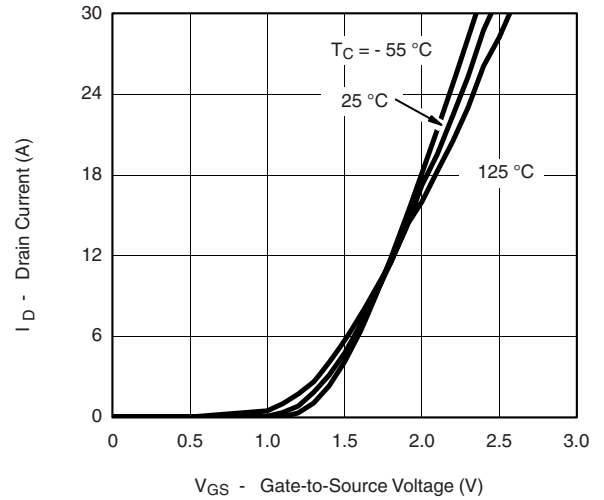
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

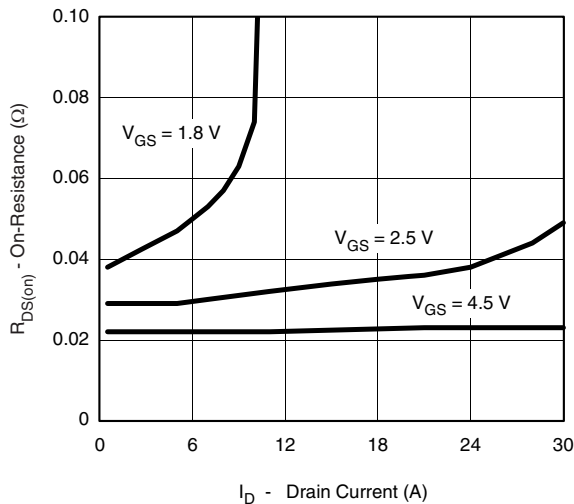
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



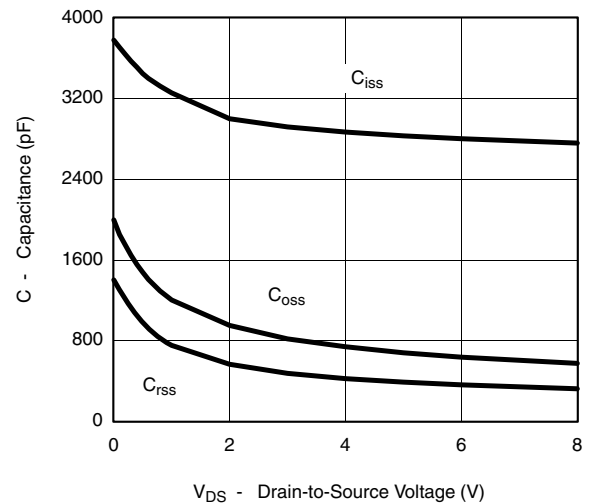
**Output Characteristics**



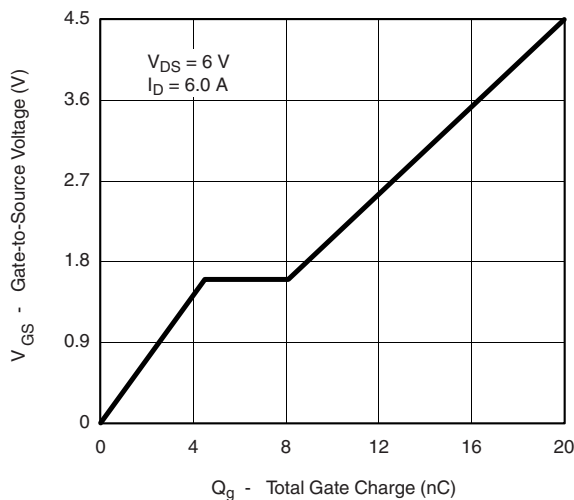
**Transfer Characteristics**



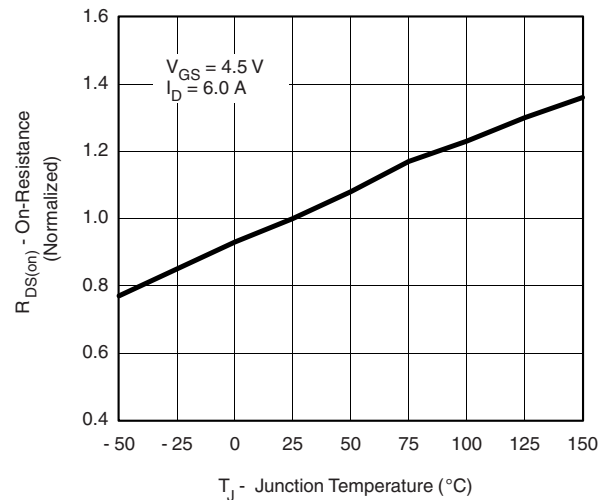
**On-Resistance vs. Drain Current**



**Capacitance**

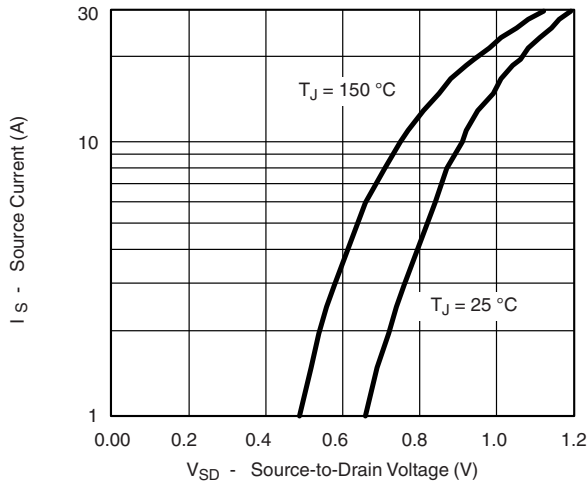


**Gate Charge**

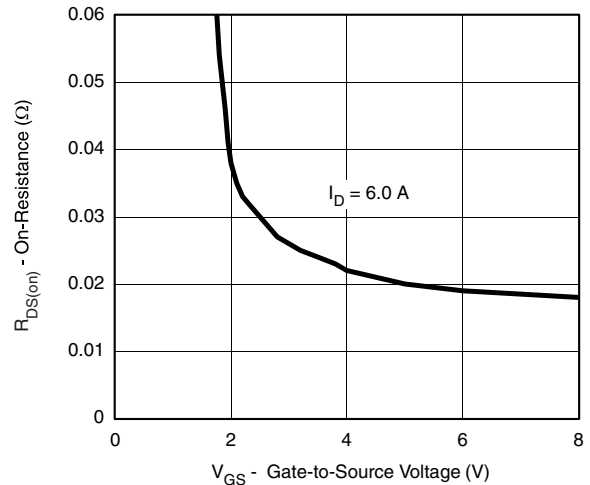


**On-Resistance vs. Junction Temperature**

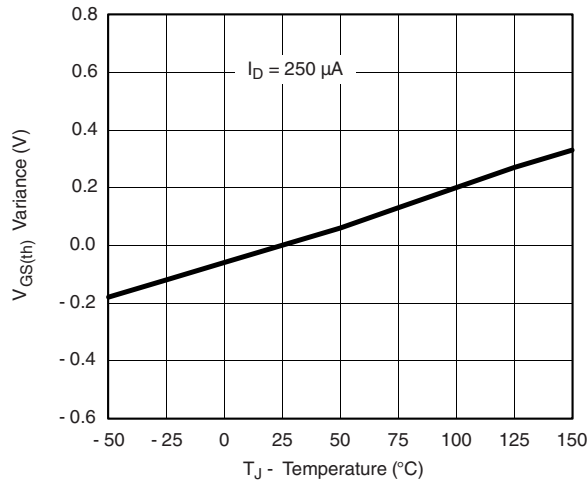
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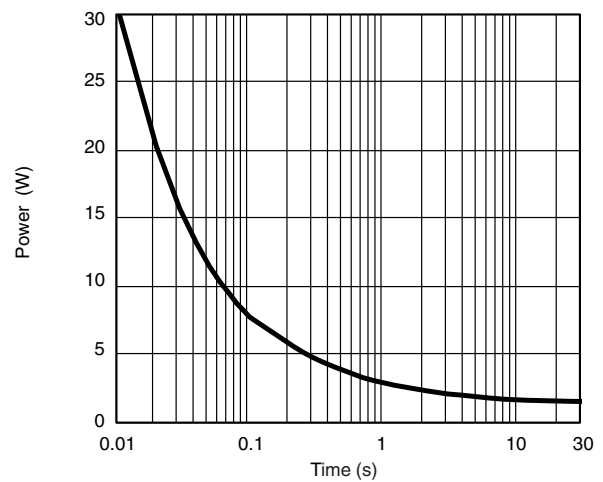
Source-Drain Diode Forward Voltage



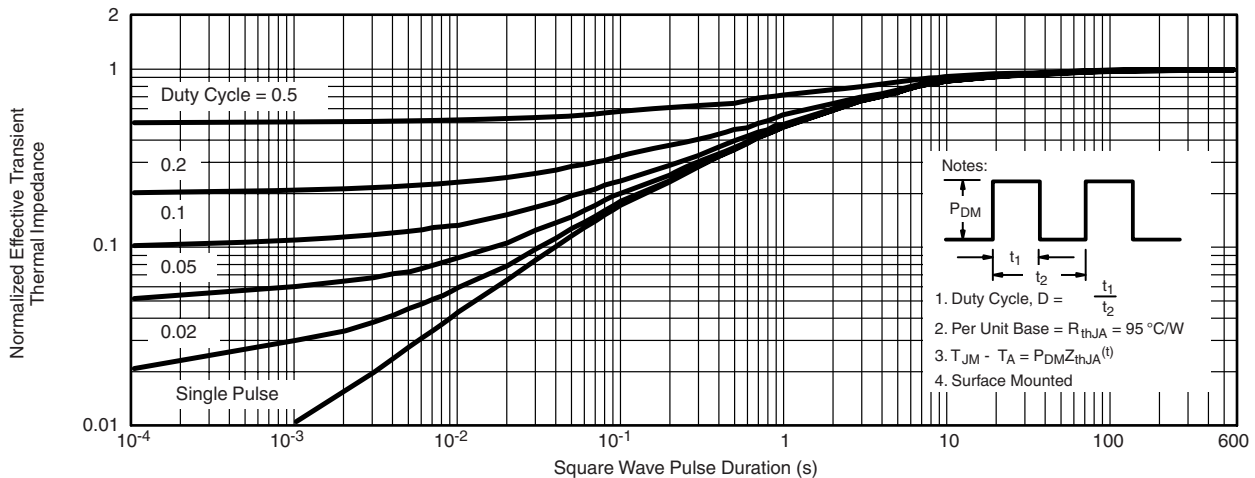
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

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